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# Density-Polarization Functional Theory of the response of a periodic insulating solid to an electric field

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# Abstract

The response of an infinite, periodic, insulating, solid to an infinitesimally small electric field is investigated in the framework of Density Functional Theory. We find that the applied perturbing potential is not a unique functional of the periodic density change: it depends also on the change in the macroscopic polarization. Moreover, the dependence of the exchange-correlation energy on polarization induces an exchange-correlation electric field. These effects are exhibited for a model semiconductor. We also show that the scissor-operator technique is an approximate way of bypassing this polarization dependence. PACS numbers: 71.10.+x; 77.20.+y; 78.20.Bh

Density-Functional Theory (DFT) [1,2] has become the standard method for first-principles calculations of the properties of solids. Within the Local Density Approximation (LDA) [2], the accuracy obtained for a wide set of properties is of the order of a few percent [3]. Notable exceptions to this gratifying picture are the cohesive energy of solids, the energy gap of semiconductors, and their dielectric susceptibility. The first of these failures is attributed to the LDA [3], while the second comes from a discontinuity in the DFT exchange-correlation potential when an electron is added across the gap [4].

The third failure is striking in that it is not easy to see whether it comes from the LDA approximation, or from some fundamental feature of DFT. At first sight, the dielectric susceptibility, being the second derivative of the ground state energy with respect to an applied electric field, should be obtained exactly within DFT. Although the corresponding potential change is linear in space, and breaks the periodicity of the solid, techniques were found to bypass this problem [5,6]. Unfortunately, the LDA results [5–7] are usually much larger (more than 10%) than the experimental data. Dal Corso, Baroni, and Resta [8] argued that any attempt to improve the LDA calculated value should go in the direction of better approximations to the true functional. The latter authors tried to compute the dielectric response of Si in the Generalized Gradient Approximation (GGA) [8], but with limited success.

Earlier, Levine and Allan had proposed a simple "LDA + scissor correction" approach to the dielectric tensor [6], in which a constant shift  $\Delta$  is imposed on the conduction bands with respect to the valence bands, to reproduce the correct band gap. The dielectric tensor in this approximation has been found to be within a few percent of the experimental data for more than a dozen semiconductors and insulators [6,7]. But, as emphasized by Dal Corso, Baroni, and Resta, there was no immediate justification within DFT of this successful procedure.

In recent work by Godby, Sham and Schlüter [9], it was shown that the exchangecorrelation potential near a semiconductor interface acquires a slow linear spatial variation, related to the discontinuity,  $\Delta$ , that occurs on addition of an electron to the bulk semiconductor. This variation corresponds to an ultra-non-local "vertex correction" in the Kohn-Sham formulation of the dielectric response of the semiconductor, and depends *crucially* on the electron density at the interface [10]. A connection between the scissor-operator correction and this linear behaviour of the exchange-correlation potential was also pointed out.

In this paper we reexamine the response of a periodic solid to an electric field within DFT, and observe that the original proof of Hohenberg and Kohn [1] does not apply to this case. We then prove the equivalent of the Hohenberg and Kohn theorem in perturbation theory, and show that knowledge of both the change in periodic density and the change in polarization are needed to recover the change of periodic potential and change of electric field that induced them. The exchange-correlation energy thus depends on the polarization, and this dependence, not taken into account previously, will generate an exchange-correlation electric field, identified with the slow linear variation of the exchange-correlation potential observed by Godby, Sham and Schlüter [9]. We then explore a simple model that exhibits the crucial features of our theory, and explain the relationship to the scissor-correction approach to the dielectric tensor.

In the DFT approach to the many-body problem, it is shown that the knowledge of the density  $n(\mathbf{r})$  of the ground-state of a system with Hamiltonian  $H_v = T + V_{e-e} + v$  (sum of the kinetic T, electron-electron interaction  $V_{e-e}$ , and one-body local potential v operators), uniquely determines the local potential  $v(\mathbf{r})$  of this Hamiltonian, up to a constant.

Unfortunately, the straightforward application of an homogeneous electric field (linear potential), to a system with a periodic potential does not allow for a ground-state solution [11]: a translation against the direction of the field by a whole number of lattice constants would always lower the electronic energy. The impossibility of a ground-state in the presence of a finite electric field renders *invalid* the original proof [1] of Density-Functional Theory for this case.

The use of perturbation theory allows us to bypass this problem. We choose to work in the long wave method [12] (an infinitesimal sinusoidal perturbation whose wavevector tends to zero). Equivalent results may be obtained using other techniques, mentioned in Ref. [12]. Atomic units, for which the electronic charge is -1, are used. The change of total potential

corresponding to an infinitesimal electric field  $\delta \mathcal{E}$  is (written in one dimension for brevity)

$$\delta v_{\mathcal{E}}(r) = \lim_{q \to 0} \delta \mathcal{E}. \frac{\sin(qr)}{q} = \lim_{q \to 0} \frac{\delta \mathcal{E}}{2iq} (e^{iqr} - e^{-iqr}). \tag{1}$$

We also allow for changes of potential that are periodic in space, with the same periodicity as the unperturbed system:  $\delta v_G(r) = \delta v(G) \cdot e^{iGr}$  with  $\delta v(G) = (\delta v(-G))^*$  where G is a non-zero vector of the reciprocal lattice. These changes of potential are obtained, in the long-wave method, from the Fourier components of the potential:

$$\delta v_G(r) = \lim_{q \to 0} \{ \delta v(G+q)e^{i(G+q)r} + \delta v(G-q)e^{i(G-q)r} \}$$
 (2)

such that  $\frac{\delta v(G)}{2} = \delta v(G+q) = \delta v(G-q)$ .

In response to these perturbations, at finite q, the system will develop changes in density described similarly by  $\delta n(G\pm q)$ . The long-wave part of this change in density, for  $q\to 0$ , will be [12]

$$\delta n_{\mathcal{P}}(r) = \lim_{q \to 0} \delta \mathcal{P} \cdot q \sin(qr),$$
 (3)

where  $\delta \mathcal{P}$  is the change of polarization for q=0.

The elaboration of a density functional theory for these perturbations must answer the following question: what quantities do we need in order to determine  $\delta \mathcal{E}$  and the set of  $\delta v(G)$  uniquely?

Since we must stay within perturbation theory for treating electric fields, we now provide a perturbative analog of the first Hohenberg-Kohn theorem [1]: the knowledge of the *change* in density everywhere uniquely determines the *change* in potential. This theorem could be proved by taking the infinitesimal limit of finite differences of the first Hohenberg-Kohn theorem [1], but this approach could not be followed for electric fields, since *only* infinitesimal electric fields are allowed. The following demonstration stays strictly within perturbation theory.

We consider the Hylleraas minimum principle [13]: a trial change in wavefunction  $\delta \phi_t$  gives an upper bound on the second-order change in energy

$$\delta^2 E \le \langle \delta \phi_t | H - E | \delta \phi_t \rangle + (\langle \delta \phi_t | \delta v | \phi \rangle + (c.c.)). \tag{4}$$

This principle is valid under the constraint  $\langle \delta \phi_t | \phi \rangle + \langle \phi | \delta \phi_t \rangle = 0$ . The minimum is reached only for the  $\delta \phi$  that is the response of the quantum-mechanical system to the change of potential  $\delta v$ . When this change of potential is a 1-body local operator, Eq.(4) becomes

$$\delta^2 E \le \langle \delta \phi_t | H - E | \delta \phi_t \rangle + \int \delta v(r) \delta n_t(r) dr, \tag{5}$$

where the change in density  $\delta n_t(r)$  is easily derived from the knowledge of the unperturbed wavefunction and the trial change in wavefunction. Now consider two changes in potentials  $\delta v_1(r)$  and  $\delta v_2(r)$  such that  $\delta v_1(r) \neq \delta v_2(r)$  + constant. The Hylleraas minimum principle applied to the perturbation  $\delta v_1(r)$  gives

$$\langle \delta \phi_1 | H - E | \delta \phi_1 \rangle + \int \delta v_1(r) \delta n_1(r) dr < \langle \delta \phi_2 | H - E | \delta \phi_2 \rangle + \int \delta v_1(r) \delta n_2(r) dr, \tag{6}$$

while for the perturbation  $\delta v_2(r)$ , a similar inequality, where 1 and 2 are interchanged, is obtained. Summing these two inequalities leads to

$$0 < \int (\delta v_1(r) - \delta v_2(r))(\delta n_2(r) - \delta n_1(r))dr. \tag{7}$$

Setting  $\delta n_1(r) = \delta n_2(r)$  would lead to a contradiction, showing that two different changes in potential must induce two different changes in density. Thus, the knowledge of  $\delta n(r)$  everywhere uniquely defines the  $\delta v(r)$  that induced it.

The same line of argument can be used in the case of perturbations of periodic systems with finite wavevector q, as previously defined. All quantities have to be normalized to the unit cell volume. This normalization, and a Fourier transform, applied to the term  $\int \delta v(r) \delta n(r) dr$  in Eq.(5), changes it into  $\Omega_{cell} \sum_{G} \{ \delta v^*(G+q) \delta n(G+q) + \delta v^*(G-q) \delta n(G-q) \}$ . The limit  $q \to 0$  is now taken, for two different perturbations described by  $\{ \delta \mathcal{E}_1, \delta v_1(G) \}$  and  $\{ \delta \mathcal{E}_2, \delta v_2(G) \}$ . The G = 0 term is isolated, and the long-wave values from Eq.(1) and (3) are used, such that :

$$0 < \frac{\Omega_{cell}}{2} \left\{ \left( \delta \mathcal{E}_1 - \delta \mathcal{E}_2 \right) \left( \delta \mathcal{P}_2 - \delta \mathcal{P}_1 \right) + \sum_{G \neq 0} \left( \delta v_1^*(G) - \delta v_2^*(G) \right) \left( \delta n_2(G) - \delta n_1(G) \right) \right\}. \tag{8}$$

If we now suppose  $\delta \mathcal{P}_1 = \delta \mathcal{P}_2$  and  $\delta n_1(G) = \delta n_2(G)$ , the expected contradiction is obtained. From this result we conclude that the change in potential and electric field can be deduced from the knowledge of the change in density and polarization that were induced by them. Note that the knowledge of the change of polarization is crucial, since it is the quantity conjugate to the change of electric field in Eq.(8): if  $\delta \mathcal{P}_1$  were allowed to be different from  $\delta \mathcal{P}_2$ , Eq.(8) could be satisfied for some  $\delta \mathcal{E}_1 \neq \delta \mathcal{E}_2$ . The dependence on polarization is a remnant of the ultra-non-local dependence on the long-wave part of the change in density, Eq.(3), that vanishes for q = 0.

Eq.(8) also shows that *if* no change in electric field is allowed, the knowledge of the polarization is not needed: a density-polarization functional theory is required for the *specific* case of the response to an electric field [14].

In the Kohn-Sham construction [2], an exchange-correlation energy functional of the density is introduced. Following the Kohn-Sham argument, now applied to the response to an electric field, this functional will depend on both the periodic density and the polarization:  $E_{xc}[n_G; \mathcal{P}]$ . This functional is defined only for values of  $\mathcal{P}$  in an infinitesimally small neighborhood of the zero-field polarization [15].

We show now that this polarization dependence of the exchange-correlation energy leads to the existence of a new "exchange-correlation electric field".

First, we mention that the treatment of the electric field as a perturbation makes use of the following link between the operator r and the derivative with respect to the wavevector [5]:

$$\delta \mathcal{E} \cdot P_c r |u_{j,k}\rangle = \delta \mathcal{E} \cdot P_c i \frac{\partial}{\partial k} |u_{j,k}\rangle \tag{9}$$

where  $P_c$  is the projector on the conduction bands, and  $u_{j,k}$  is the periodic part of the Bloch function of band j with wavevector k.

Also, the recent theory of polarization proposed by King-Smith and Vanderbilt [16] leads to the expression for the polarization [15]

$$\mathcal{P} = \sum_{j} 2i \int \langle u_{j,k} | \frac{\partial}{\partial k} | u_{j,k} \rangle \frac{dk}{2\pi}, \tag{10}$$

where the sum is over the valence bands.

When wavefunctions are varied in order to find the Kohn-Sham self-consistent equations, the exchange-correlation energy changes, owing to the implicit dependence of the density on wavefunctions, but also owing to the implicit dependence of the polarization on wavefunctions (see Eq.10). The term  $P_c \delta v_{xc} |u_{j,k}\rangle$  that appears in the perturbative equivalent of the Kohn-Sham equation (the Sternheimer equation [5]) is replaced by

$$P_c \, \delta v_{xc} |u_{j,k}\rangle + \delta \mathcal{E}_{xc} P_c \, i \, \frac{\partial}{\partial k} |u_{j,k}\rangle$$
 (11)

where  $\delta \mathcal{E}_{xc} = \frac{\partial^2 E_{xc}}{\partial \mathcal{P}^2} \delta \mathcal{P} + \sum_G \frac{\partial^2 E_{xc}}{\partial \mathcal{P} \partial n_G} \delta n_G$ .

The second term of Eq.(11), missing in previous theories of the dielectric constant [5], is to be interpreted as an additional electric field (compare with Eq.(9)), created by the polarization dependence of the exchange-correlation energy. It vanishes in zero applied electric field.

We will now analyze the model one-dimensional semiconductor used by Godby and Sham in Ref. [10], and show that it exhibits the main features of our theory: 1) the knowledge of the density change alone is not sufficient to deduce the periodic potential change and electric field change; 2) an exchange-correlation electric field appears.

In this model, the periodic solid plus electric field is treated by the long-wave method in a supercell consisting of N basic unit cells of length a. The external potential plus the Hartree potential  $V_{\text{ext}}(x) + V_{\text{H}}(x)$  is taken to be the sum of two different contributions:  $V_0 \cos(\frac{2\pi x}{a}) + \lambda \sin(\frac{2\pi x}{Na})$ . The first term has the periodicity of one unit cell, while the second, with the periodicity of the supercell, corresponds to a slowly varying potential of amplitude  $\lambda$ . For an infinitely long supercell, the second term mimics the action of an electric field.

The self-energy operator is taken to be the non-local potential:  $\Sigma(x, x', \omega) = \frac{f(x)+f(x')}{2}g(|x-x'|)$  where  $f(x) = -F_0[1-\cos(2\pi x/a)]$  is a negative function with the periodicity of one unit cell and g(y) is a normalized gaussian of width w=2 a.u.

We keep the same set of parameters as in Ref. [10]. First, the many-body problem is solved by direct diagonalization of the equations containing the self-energy operator, using a plane-wave basis set and a Brillouin zone sampling at the  $\Gamma$  point only. From this result, we construct an *exact* density functional theory by determining the local potential  $V_{\text{eff},1}(x)$  which, when filled with *non-interacting* electrons (no self-energy operator), reproduces the same electron density as in the many-body case (see Fig. 4 of Ref. [10]). Standard iterative non-linear optimization techniques are used for that purpose. Independently, we also extract the (polarized) density of the single unit cell  $\pm \frac{1}{2}a$  where the slowly varying potential is most linear and, again using optimization techniques, we reproduce this density with *another* potential,  $V_{\text{eff},2}(x)$ , having period a. In this case, to retain the sampling of the Brillouin zone at the  $\Gamma$  point, we repeat the density periodically in the supercell. The only problem in reproducing the "target" density comes from the slight non-linearity of the slowly varying potential, and disappears progressively for larger supercells. Fig. 1 presents the results obtained with a 80a supercell and  $\lambda = 0.95$  eV, for which the r.m.s. difference between the target and computed density is 4 parts per thousand.

This example illustrates that the action of a linear potential  $\Delta(V_{\rm ext} + V_{\rm H})$ , superimposed on a periodic potential, in the case of an interacting-electron model system can be mimicked by two different potentials  $\Delta V_{\rm eff,1}$  and  $\Delta V_{\rm eff,2}$ , acting upon the corresponding non-interacting electron system, in contrast to a naïve application of DFT theorems. However,  $\Delta V_{\rm eff,2}$  is not able to reproduce the polarization (0.037 electrons), associated with the long-wavelength charge density. Moreover,  $\Delta(V_{\rm ext} + V_{\rm H})$  and the linear component  $\Delta V_{\rm eff,1}^{\rm linear}$  of the Kohn-Sham potential  $\Delta V_{\rm eff,1}$  differ by 15%, owing to the existence of the exchange-correlation electric field.

We now discuss briefly the implications of our theory for practical calculations. LDA or GGA techniques can be used to approximate the periodic-density dependence of  $E_{xc}$ . Unfortunately, since the homogeneous electron gas is metallic, we do not see any easy way to modify LDA or GGA in order to obtain a polarization-dependent exchange-correlation energy, that would generate the second term in Eq.(11). Nevertheless, our theory allows

the scissor-operator correction to be understood as an *approximate* way of *bypassing* this dependence.

Indeed, in Ref. [10], it was shown that the effect of a slowly varying potential  $\Delta V$  that induces transitions between valence and conduction bands with a gap  $E_g$  (see Eq.(10) of Ref. [10]) is approximately equivalent to the effect of a slowly varying potential  $\Delta V + \Delta V_{xc}$  that induces transitions between valence and conduction bands with a gap  $E_g^{DFT}$  (see Eq.(11) of Ref. [10]). Hence, the exact density-polarization functional theory calculation in a field  $\delta \mathcal{E} + \delta \mathcal{E}_{xc}$ , with a gap  $E_g^{DFT}$ , can be approximately replaced by a LDA calculation in a field  $\delta \mathcal{E}$ , with a modified gap  $E_g$ : this is the "LDA + scissor correction", which gives a dielectric constant for Si of 11.2 (Experiment 11.4-11.7, LDA 12.9-13.5, GGA 12.4-12.6) [6–8].

In conclusion, because the original Hohenberg-Kohn theorem is not valid for the case of the response to an homogeneous electric field, we have set up a density-polarization functional theory, of which an approximate form is the "LDA + scissor correction".

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# REFERENCES

- [1] P. Hohenberg and W. Kohn, Phys. Rev. <u>136</u>, B864 (1964).
- [2] W. Kohn and L.J. Sham, Phys. Rev. <u>140</u>, A1133 (1965).
- [3] R.O. Jones and O. Gunnarsson, Rev. Mod. Phys. <u>61</u>, 689 (1989). W.E. Pickett, Comp. Phys. Rep. <u>9</u>, 115 (1989).
- [4] L.J. Sham and M. Schlüter, Phys. Rev. Lett. <u>51</u>, 1888 (1983); J.P. Perdew and M. Levy, Phys. Rev. Lett. <u>51</u>, 1884 (1983).
- [5] S. Baroni and R. Resta, Phys. Rev. B <u>33</u>, 7017 (1986); M.S. Hybertsen and S.G. Louie,
  Phys. Rev. B. <u>34</u>, 5390 (1986); P. Giannozzi *et al.*, Phys. Rev. B. <u>43</u>, 7231 (1991); C.
  Lee, Ph. Ghosez, and X. Gonze, Phys. Rev. B. <u>50</u>, 13379 (1994); and references therein.
- [6] Z. H. Levine and D. C. Allan, Phys. Rev. Lett. <u>63</u>, 1719 (1989); Phys. Rev. B. <u>43</u>, 4187 (1991).
- [7] Z. H. Levine and D. C. Allan, Phys. Rev. B <u>44</u>, 12781 (1991); J. Chen, Z.H. Levine, and J.W. Wilkins, Phys. Rev. B <u>50</u>, 11514 (1994).
- [8] A. Dal Corso, S. Baroni, and R. Resta, Phys. Rev. B. <u>49</u>, 5323 (1994).
- 9 R.W. Godby, L.J. Sham and M. Schlüter, Phys. Rev. Lett. <u>65</u>, 2083 (1990).
- [10] R.W. Godby and L.J. Sham, Phys. Rev. B <u>49</u>, 1849 (1994).
- [11] R.W. Nunes and D. Vanderbilt, Phys. Rev. Lett. <u>73</u>, 712 (1994).
- [12] R. Martin, Phys. Rev. B <u>5</u>, 1607 (1972); Phys. Rev. B <u>9</u>, 1998 (1974); R. Resta and K. Kunc, Phys. Rev. B <u>34</u>, 7146 (1986).
- [13] E.A. Hylleraas, Z. Phys. <u>65</u>, 209 (1930); J.O. Hirschfelder, W. Byers Brown, and S.T. Epstein, Advances in Quantum Chemistry (Academic Press, New York, 1964), vol. 1, p.278.

- [14] As usual in the theory of electromagnetism, the electric displacement field has to be used instead of the electric field if the electron-electron interaction is not short-ranged, which is the case for the Coulombic interaction. See L.D. Landau and E.M. Lifshits, Electrodynamics of Continuous Media (Pergamon Press, 1960). All the results of our theory are unaffected by this replacement.
- [15] The modern theory of polarization [16] defines it only up to a quantum. This feature is of no consequence for the present theory, since only infinitesimal changes in polarization are considered.
- [16] R.D. King-Smith and D. Vanderbilt, Phys. Rev. B <u>47</u>, 1651 (1993); D. Vanderbilt and R.D. King-Smith, Phys. Rev. B <u>48</u>, 4442 (1993); R. Resta, Rev. Mod. Phys. <u>66</u>, 899 (1994).

#### FIGURE CAPTIONS

Fig.1 The unit cell of our model one-dimensional semiconductor, where the slowly varying applied potential  $\Delta(V_{\rm ext} + V_{\rm H})$ , that changes the interacting electron density by  $\Delta n$ , is the most linear. Both  $\Delta V_{\rm eff,1}$  and  $\Delta V_{\rm eff,2}$ , used in the non-interacting Kohn-Sham equations, yield the same  $\Delta n$ .  $\Delta V_{\rm eff,2}$  is a periodic potential with no linear slope, while  $\Delta V_{\rm eff,1}$ , whose linear part is  $\Delta V_{\rm eff,1}^{\rm linear}$ , reproduces not only  $\Delta n$  but also the change of polarization due to  $\Delta(V_{\rm ext} + V_{\rm H})$ . This illustrates the need for polarization-dependence in  $E_{xc}$ . For clarity, the potential curves have been aligned so that they all start from zero.

